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Vishay Siliconix

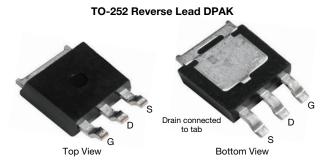
Automotive N-Channel 100 V (D-S) 175 °C MOSFET

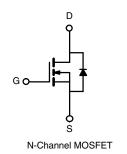
PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.025			
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.029			
I _D (A)	40			
Configuration	Single			
Package	TO-252 Reverse Lead DPAK			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>







ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted	d)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C a	l _D	40		
Continuous Drain Current	T _C = 125 °C		26		
Continuous Source Current (Diode Conduction) a		I _S	40	Α	
Pulsed Drain Current ^b		I _{DM}	160		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	80	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	W	
Maximum Fower Dissipation -	T _C = 125 °C	P_{D}	45	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	-	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	50	-	-	Α
Drain-Source On-State Resistance a		V _{GS} = 10 V	I _D = 40 A	-	0.019	0.025	Ω
	Ь	V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.050	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.063	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.021	0.029	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 40 A	-	73	=.	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2703	3380	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	312	390	pF
Reverse Transfer Capacitance	C _{rss}			-	127	160	
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_D = 40 \text{ A}$	-	8.2	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	13	-	
Gate Resistance	R_g	f = 1 MHz		0.9	1.8	3.1	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	11	17	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_L = 1.25 \Omega$ $I_D \cong 40 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	17	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	160	Α
Forward Voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.9	1.5	V

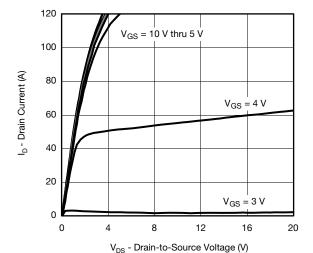
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

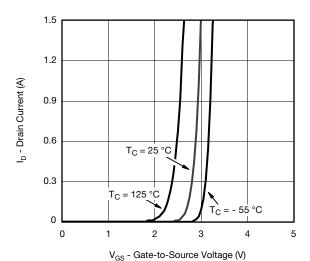
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



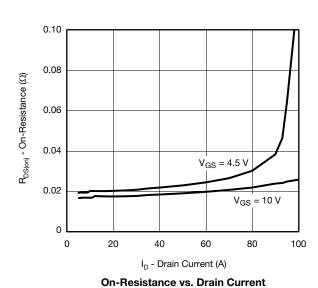
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

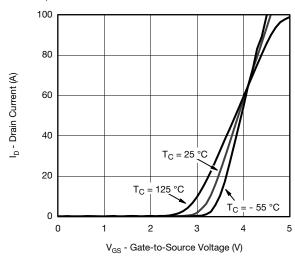


Output Characteristics

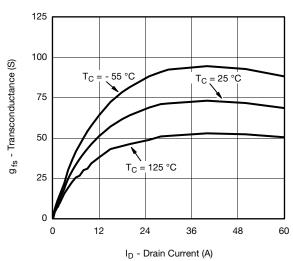


Transfer Characteristics

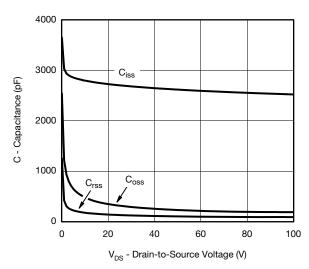




Transfer Characteristics

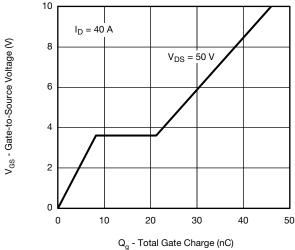


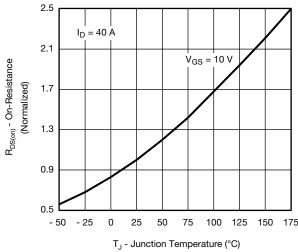
Transconductance



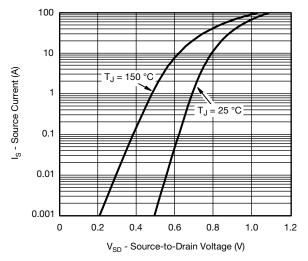


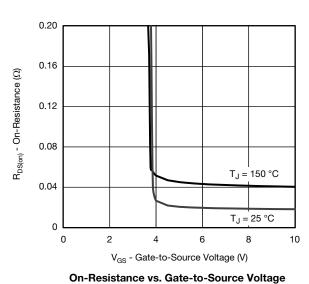
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



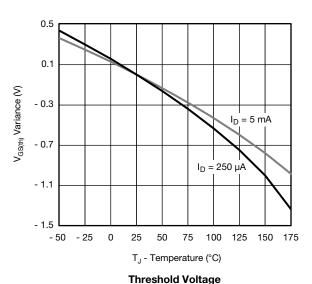


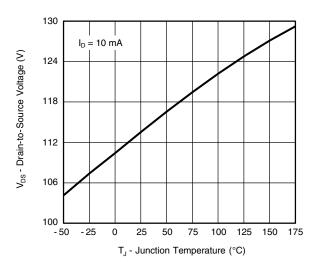
Gate Charge On-Resistance vs. Junction Temperature





Source Drain Diode Forward Voltage

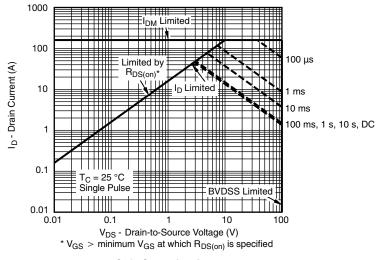




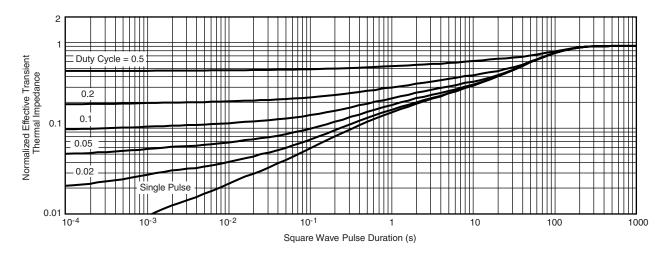
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



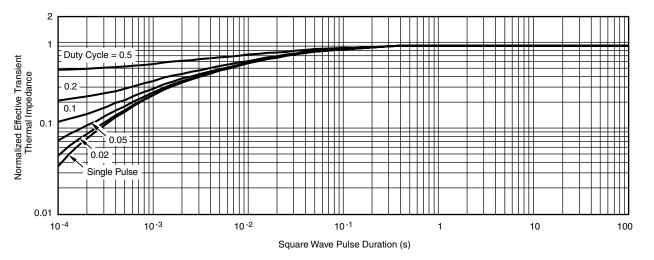
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg269060.



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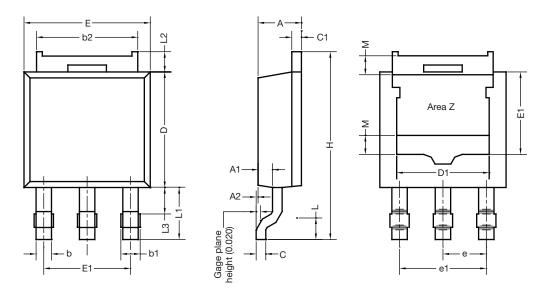
REVISION HISTORY a				
REVISION	DATE	DESCRIPTION OF CHANGE		
F	04-Aug-15	Revised R _g minimum limit		

Note

a. As of April 2014

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TO-252 Reverse Lead Case Outline



Notes

- Dimension L3 for reference only
- Area Z: unplated area more than 80 % heatsink area and for partial plating part only

DIM.	MILI	LIMETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.23	2.33	0.088	0.092	
A1	0.64	0.89	0.025	0.035	
A2	0.03	0.18	0.001	0.007	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.49	5.00	0.177	0.197	
E	6.48	6.73	0.255	0.265	
E1	4.32	-	0.170	-	
е	2.28 BSC		0.090 BSC		
e1	4.	.57 BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 BSC		
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
М	-	1.00 (reference only)	-	0.039 (reference only	

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DWG: 5894

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